

MA2S111 (Tentative)

Silicon epitaxial planer type

For switching circuits

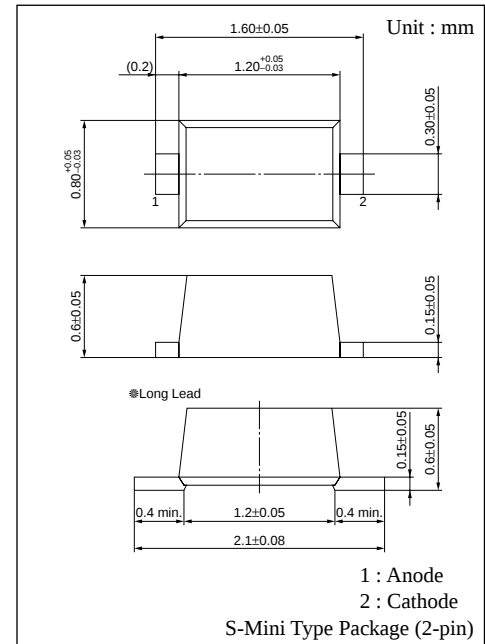
■ Features

- Small S-Mini type 2-pin package
- High-density mounting possible
- Short reverse recovery period t_{rr}
- Small capacity between pins, C_t

■ Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	80	V
Peak reverse voltage	V_{RM}	80	V
Average forward current	I_F (AV)	100	mA
Peak forward current	I_{FM}	225	mA
Non-repetitive peak forward surge current	I_{FSM}^*	500	mA
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	- 55 to +150	$^\circ\text{C}$

* $t = 1\text{s}$



Marking Symbol : A

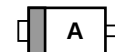
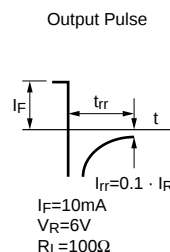
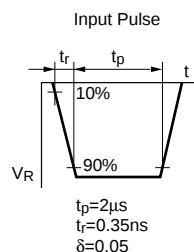
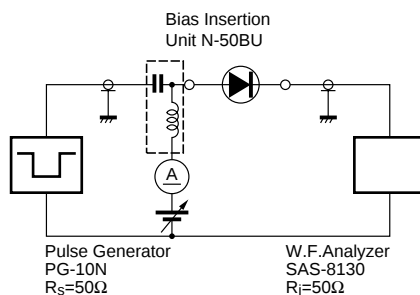
■ Electrical Characteristics ($T_a = 25^\circ\text{C}$)

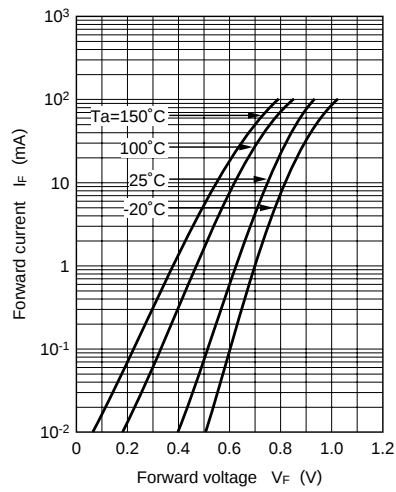
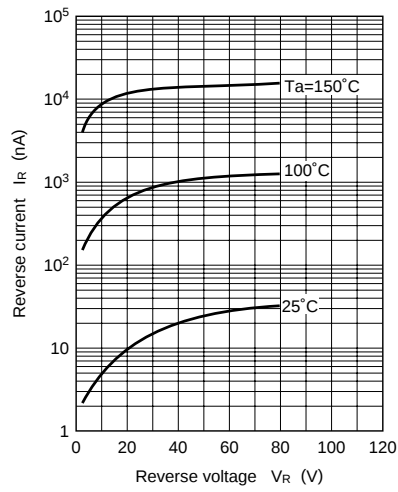
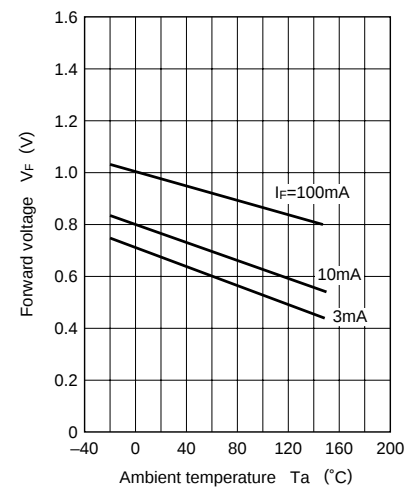
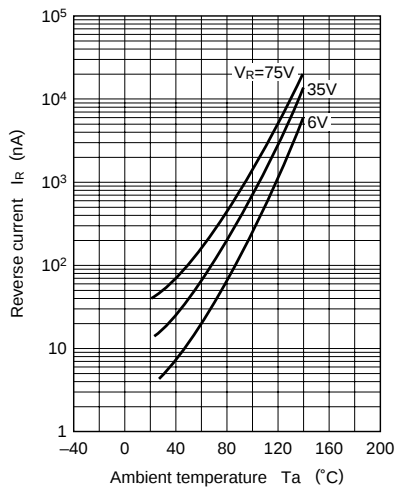
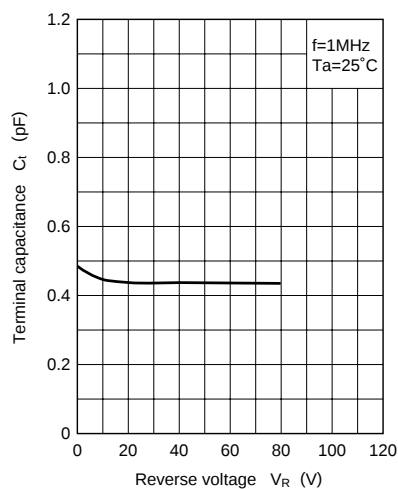
Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	$V_R = 75\text{V}$			0.1	μA
Forward voltage (DC)	V_F	$I_F = 100\text{mA}$		0.95	1.2	V
Reverse voltage (DC)	V_R	$I_R = 100\mu\text{A}$	80			V
Terminal capacitance	C_t	$V_R = 0\text{V}, f = 1\text{MHz}$		0.6	1.2	pF
Reverse recovery time	t_{rr}^*	$I_F = 10\text{mA}, V_R = 6\text{V}$ $I_{rr} = 0.1 \cdot I_R, R_L = 100\Omega$			3	ns

Note 1. Rated input/output frequency : 100MHz

2. * : t_{rr} measuring circuit

■ Marking



$I_F - V_F$  $I_R - V_R$  $V_F - T_a$  $I_R - T_a$  $C_t - V_R$  $I_F(\text{surge}) - t_W$ 